Abstracts

Improved Elementary Cell GaAs Power FET Structure

P. Baudet. "Improved Elementary Cell GaAs Power FET Structure." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 3-5.

An improved design for the elementary cell of X-band power GaAs FETs is described. It includes: a buffer layer, a graded doping profile, an offset recessed gate structure, a multifinger high density gate structure and via holes. Furthermore, three different types of source interconnections for the interdigitated cell will be compared.

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